

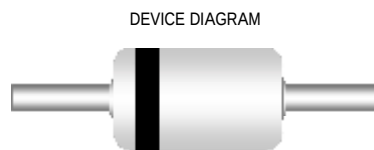
Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
P_D	Power Dissipation	500	mW
T_{STG}	Storage Temperature Range	-65 to +150	$^\circ\text{C}$
T_J	Operating Junction Temperature	+150	$^\circ\text{C}$
W_{IV}	Working Inverse Voltage	75	V
I_O	Average Rectified Current	150	mA
I_{FM}	Non-repetitive Peak Forward Current	450	mA
I_{FSURGE}	Peak Forward Surge Current (Pulse Width = 1.0 μsecond)	2	A

These ratings are limiting values above which the serviceability of the diode may be impaired.



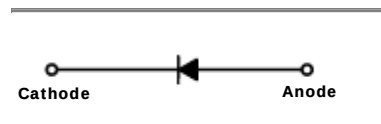
AXIAL LEAD
DO35



DEVICE DIAGRAM

Specification Features:

- § Fast Switching Device ($T_{RR} < 4.0 \text{ nS}$)
- § DO-35 Package (JEDEC)
- § Through-Hole Device Type Mounting
- § Hermetically Sealed Glass
- § Compression Bonded Construction
- § All External Surfaces Are Corrosion Resistant And Leads Are Readily Solderable
- § RoHS Compliant
- § Solder Hot Dip Tin (Sn) Terminal Finish
- § Cathode Indicated By Polarity Band



ELECTRICAL SYMBOL

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Limits		Unit
			Min	Max	
B_V	Breakdown Voltage	$I_R = 100 \mu\text{A}$ $I_R = 5 \mu\text{A}$	100 75		Volts
I_R	Reverse Leakage Current	$V_R = 20\text{V}$ $V_R = 75\text{V}$		25 5	nA μA
V_F	Forward Voltage	$I_F = 10\text{mA}$		1.0	Volts
T_{RR}	Reverse Recovery Time	$I_F = 10\text{mA}$, $V_R = 6\text{V}$ $R_L = 100\Omega$ $I_{RR} = 1\text{mA}$		4	nS
C	Capacitance	$V_R = 0\text{V}$, $f = 1\text{MHz}$		4	pF

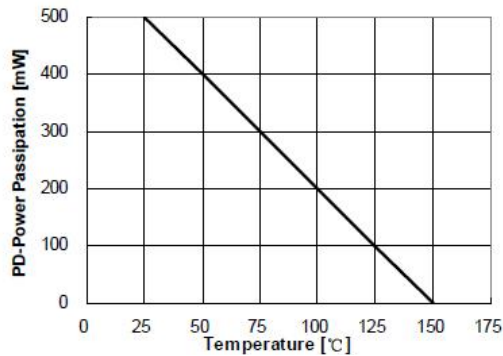
Typical Characteristics


Figure 1. Power Dissipation vs Ambient Temperature
Valid provided leads at a distance of 0.8mm from case are kept at ambient temperature

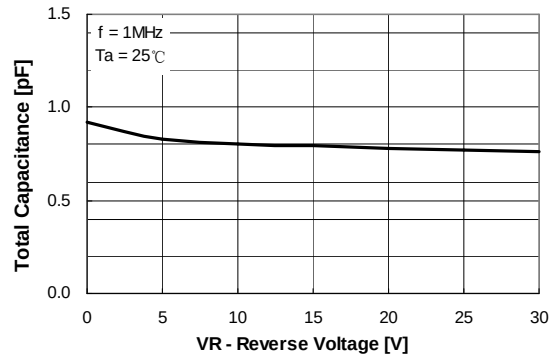


Figure 2. Total Capacitance

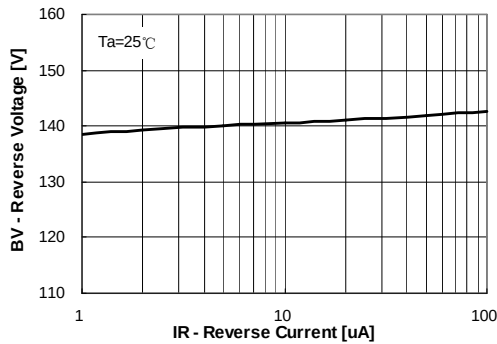


Figure 3. Reverse Voltage vs Reverse Current
BV – 1.0uA to 100uA

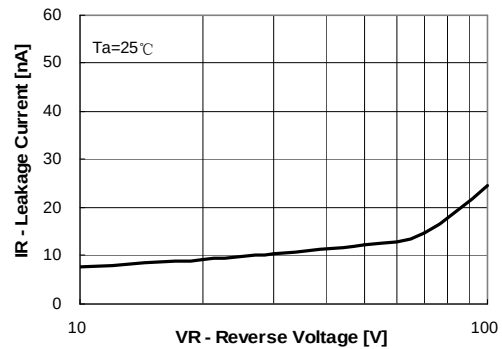


Figure 4. Reverse Current vs Reverse Voltage
IR – 10V to 100V

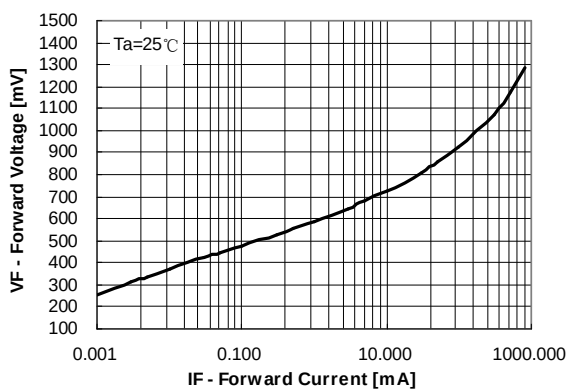


Figure 5. Forward Voltage vs Forward Current
VF – 0.001mA to 800mA

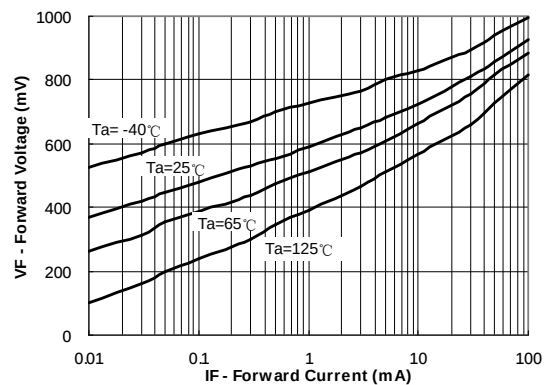
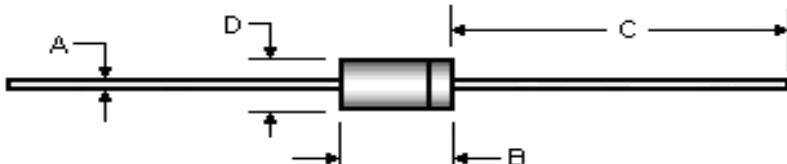


Figure 6. Forward Voltage vs Ambient Temperature
VF – 0.01mA to 100mA (-40 to +125 Deg C)

Package Outline

Package	Case Outline				
DO-35					
	DIM	DO-35			
		Millimeters		Inches	
		Min	Max	Min	Max
	A	0.46	0.55	0.018	0.022
	B	---	4.00	---	0.157
	C	25.40	38.10	1.000	1.500
	D	1.53	2.00	0.060	0.079

- Notes:**
1. All dimensions are within JEDEC standard.
 2. DO35 polarity denoted by cathode band.

NOTICE

The information presented in this document is for reference only. Involving product optimization and productivity improvement, ChipNobo reserves the right to adjust product indicators and upgrade some technical parameters. ChipNobo is entitled to be exempted from liability for any delay or non-delivery of the information disclosure process that occurs.

本文件中提供的信息仅供参考。涉及产品优化和生产效率改善，ChipNobo 有权调整产品指标和部分技术参数的升级，所出现信息披露过程存在延后或者不能送达的情形，ChipNobo 有获免责权。

The product listed herein is designed to be used with residential and commercial equipment, and do not support sensitive items and specialized equipment in areas where sanctions do exist. ChipNobo Co., Ltd or anyone on its behalf, assumes no responsibility or liability for any damages resulting from improper use.

此处列出的产品旨在民用和商业设备上使用，不支持确有制裁地区的敏感项目和特殊设备，ChipNobo 有限公司或其代表，对因不当使用而造成的任何损害不承担任何责任。

For additional information, please visit our website <http://www.chipnobo.com>, or consult your nearest Chipnobo sales office for further assistance.

欲了解更多信息，请访问我们的网站 <http://www.chipnobo.com>，或咨询离您最近的 Chipnobo 销售办事处以获得进一步帮助。